





N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- . ESD Protected up to 2kV
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 standards for High Reliability

Mechanical Data

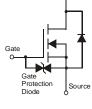
- Case: SOT-523
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.002 grams (approximate)

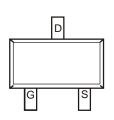




Top View

SOT-523





Equivalent Circuit

Top View

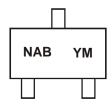
Ordering Information (Note 3)

Part Number	Case	Packaging
DMN2004TK-7	SOT-523	3000/Tape & Reel

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.
- 3. For packaging details, go to our website at http://www.diodes.com.

Marking Information



NAB = Product Type Marking Code YM = Date Code Marking Y = Year (ex: T = 2006) M = Month (ex: 9 = September)

Date Code Key

Year	200	6	2007		2008	20	09	2010		2011	2	2012
Code	Т		U		V	V	٧	Χ		Υ		Z
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings @T_A = 25°C unless otherwise specified

Charac	teristic		Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±8	V
Drain Current (Note 4)	Steady State	$T_A = 25$ °C $T_A = 85$ °C	I _D	540 390	mA
Pulsed Drain Current (Note 5)			I _{DM}	1.5	A

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 4)	P_D	150	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	833	°C/W
Operating and Storage Temperature Range	T_{J}, T_{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

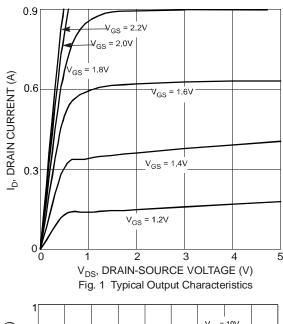
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)					_		
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 10\mu A$	
Zero Gate Voltage Drain Current	1	_	0.8	300	nA	$V_{DS} = 16V, V_{GS} = 0V$	
Zero Gate Voltage Brain Gurrent	I _{DSS}	_	0.9	_	nA	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_		±1	μΑ	$V_{GS} = \pm 4.5V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)			_	_			
Gate Threshold Voltage	V _{GS(th)}	0.5	_	1.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
			0.4	0.55		$V_{GS} = 4.5V, I_D = 540mA$	
Static Drain-Source On-Resistance	R _{DS (ON)}	_	0.5	0.70	Ω	$V_{GS} = 2.5V, I_D = 500mA$	
			0.7	0.9		V _{GS} = 1.8V, I _D = 350mA	
Forward Transfer Admittance	Y _{fs}	200	_	_	ms	$V_{DS} = 10V, I_D = 0.2A$	
Diode Forward Voltage (Note 6)	V_{SD}	0.5	_	1.4	V	$V_{GS} = 0V, I_{S} = 115mA$	
DYNAMIC CHARACTERISTICS			_	_			
Input Capacitance	C _{iss}	_	_	150	pF	101/1/	
Output Capacitance	Coss	_	_	25	pF	$V_{DS} = 16V, V_{GS} = 0V$ -f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	_	20	pF		
SWITCHING CHARACTERISTICS							
Turn-On Delay Time	t _{d(on)}		8.5	_	ns		
Rise Time	t _r	_	9.1	_	ns	$V_{DD} = 10V$, $R_L = 47\Omega$, $I_D = 200$ mA,	
Turn-Off Delay Time	t _{d(off)}	_	51	_	ns	$V_{GEN} = 4.5V$, $R_G = 10\Omega$	
Fall Time	t _f	_	28	_	ns		

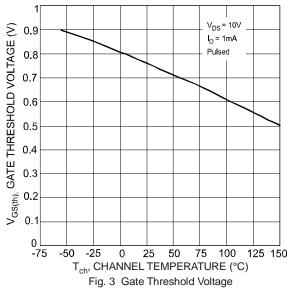
Notes:

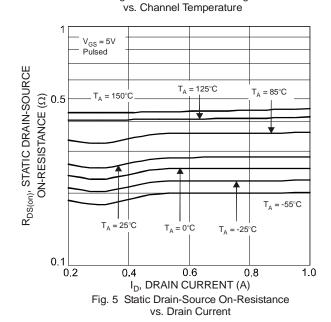
4. Device mounted on FR-4 PCB. 5. Pulse width \leq 10 μ S, Duty Cycle \leq 1%

6. Short duration pulse test used to minimize self-heating effect.









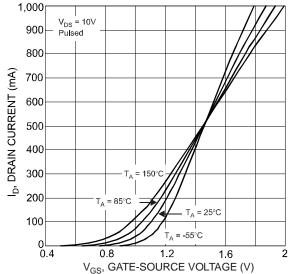


Fig. 2 Reverse Drain Current vs. Source-Drain Voltage

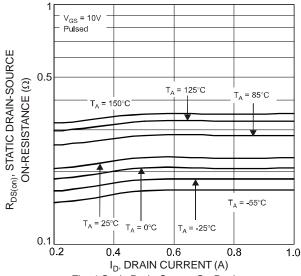


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

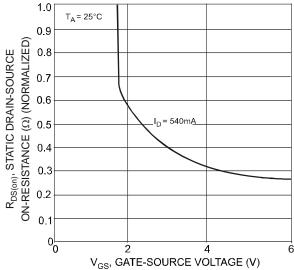


Fig. 6 Static Drain-Source, On-Resistance vs. Gate-Source Voltage



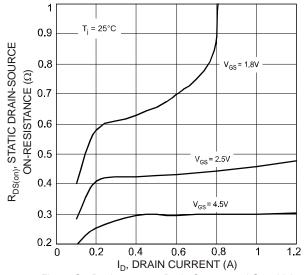


Fig. 7 On-Resistance vs. Drain Current and Gate Voltage

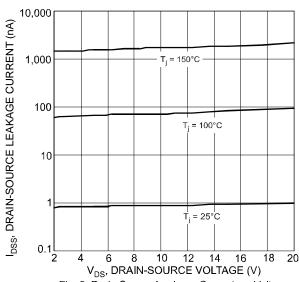


Fig. 9 Drain Source Leakage Current vs. Voltage

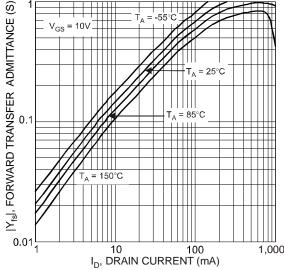


Fig. 11 Forward Transfer Admittance vs. Drain Current

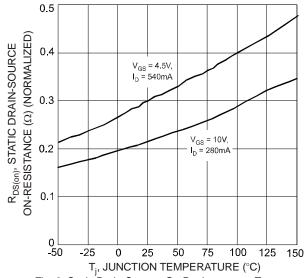


Fig. 8 Static Drain-Source, On-Resistance vs. Temperature

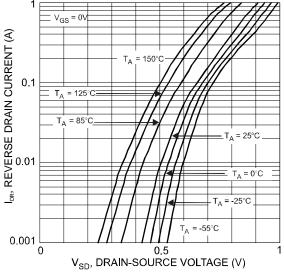
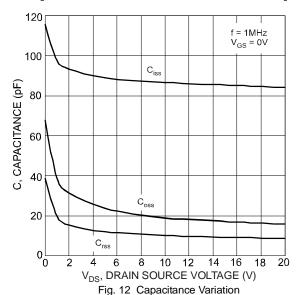
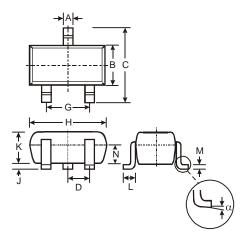


Fig. 10 Reverse Drain Current vs. Source-Drain Voltage



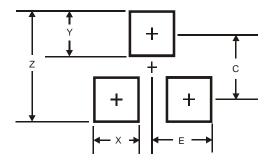


Package Outline Dimensions



SOT-523								
Dim	Min	Max	Тур					
Α	0.15	0.30	0.22					
В	0.75	0.85	0.80					
C	1.45	1.75	1.60					
D			0.50					
G	0.90	1.10	1.00					
H	1.50	1.70	1.60					
7	0.00	0.10	0.05					
K	0.60	0.80	0.75					
L	0.10	0.30	0.22					
М	0.10	0.20	0.12					
N	0.45	0.65	0.50					
α	0°	8°	_					
All Dimensions in mm								

Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.8
X	0.4
Υ	0.51
С	1.3
F	0.7



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